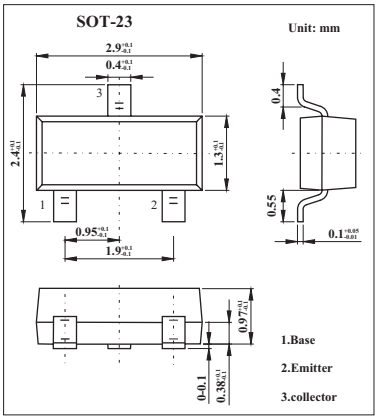
Switching Transistors

FMMT4126



■ Features

- Switching transistors.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-4	V
Collector current	I_C	-200	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j,T_{stg}	-55 to +150	℃

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10□A,	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10□A,	-4			V
Collector cutoff current	I_{CBO}	V_{CE}=-20V			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V			-50	nA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA			-0.4	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C=-50mA, I_B=-5mA			-0.95	V
DC current gain *	h_{FE}	I_C=-2mA, V_{CE}=-1V	120		360	
Current-gain-bandwidth product	f_T	I_C=-10mA, V_{CE}=-20V f=100MHz	250			MHz
Output capacitance	C_{obo}	V_{CB}=-5V, I_E=0, f=140KHz			4.5	pF
Input capacitance	C_{ibo}	V_{BE}=-0.5V, I_C=0, f=140KHz			10	pF
Noise figure	NF	V_{CE}=-5V I_C=-200□A,R_g=-2K? f=30Hz to 15KHz at -3dB points			4	dB
Small signal current transfer	h_{fe}	I_C=-2mA, V_{CE}=-1V, f=1KHz	120	180		
Delay time	t_d	V_{CC}=-3V, I_C=-10mA,I_{B1}=-1mA $V_{BE(off)}$=-0.5V			25	ns
Rise time	t_r				18	ns
Storage time	t_s	V_{CC}=-3V, I_C=-10mA I_{B1}= I_{B2}=-1mA			140	ns
Fall time	t_f				15	ns

* Pulse test: tp ⩽ 300 μs; d ⩽ 0.02.

■ Marking

Marking	ZE